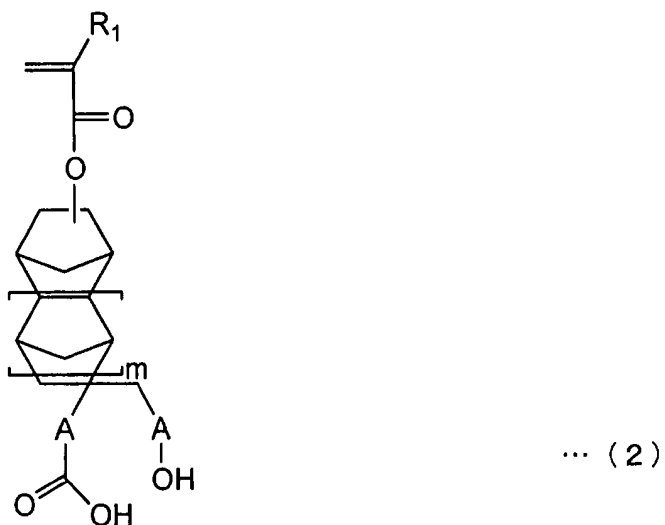


AMENDMENTS TO THE CLAIMS

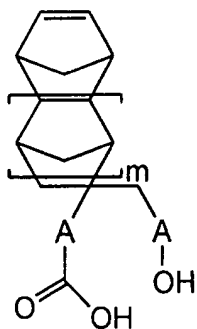
Claim 1. (Currently Amended) A negative-working resist material comprising at least a polymeric compound and an acid generating agent, wherein the polymeric compound has a polymerizable unit selected from the group consisting of polymerizable units represented by general formulae (1) to (3): ~~having a polymerizable main chain moiety and a hydroxy acid moiety bound to said main chain moiety as a side chain component, the hydroxyl moiety is bound to the main chain moiety via only one carbon in the carbon skeleton of the hydroxy acid, and a space of such size as to permit an alkali substance to approach a binding site between the hydroxy acid moiety and the main chain moiety is not present between the hydroxy acid moiety and the main chain moiety.~~



wherein R_1 is a hydrogen atom or an alkyl group having 1 to 5 carbon atoms, and A is a nitrogen atom, a sulfur atom, or an alkyl group having 1 to 21 carbon atoms;



wherein R₁ is a hydrogen atom or an alkyl group having 1 to 5 carbon atoms, A is a nitrogen atom, a sulfur atom, or an alkyl group having 1 to 21 carbon atoms, and m is an integer of 0 to 3;

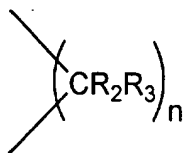


... (3)

wherein A is a nitrogen atom, a sulfur atom, or an alkyl group having 1 to 21 carbon atoms, and m is an integer of 0 to 3.

Claims 2 to 6. (Canceled)

Claim 7. (Currently Amended) The negative-working resist material according to claim [[4]] 1, wherein A in the general formula representing the polymerizable unit is an alkyl group represented by the following general formula (4):



... (4)

wherein each of R₂ and R₃ is an alkyl group having 1 to 3 carbon atoms, and n is an integer of 1 to 3.

Claim 8. (Original) The negative-working resist material according to claim 7, wherein the alkyl group represented by R₂ and/or R₃ is a fluoroalkyl group.

Claim 9. (Currently Amended) The negative-working resist material according to claim [[4]] 1, wherein A in the general formula representing the polymerizable unit is an alkyl group having 1 to 5 carbon atoms.

Claims 10 to 15. (Canceled)

Claim 16. (Original) A method of forming a resist pattern, which comprises a step of forming a photoresist pattern by forming at least a photoresist layer with the negative-working resist material of claim 1 on a substrate and subjecting the photoresist layer to light exposure and development treatments to form a predetermined photoresist pattern.